

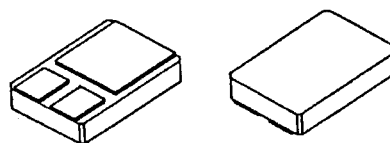


PRELIMINARY

SOLID STATE DEVICES, INC14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**SFF801R2****Designer's Data Sheet****FEATURES:**

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed surface mount package
- Low inductance package
- TX, TXV and Space Level screening available

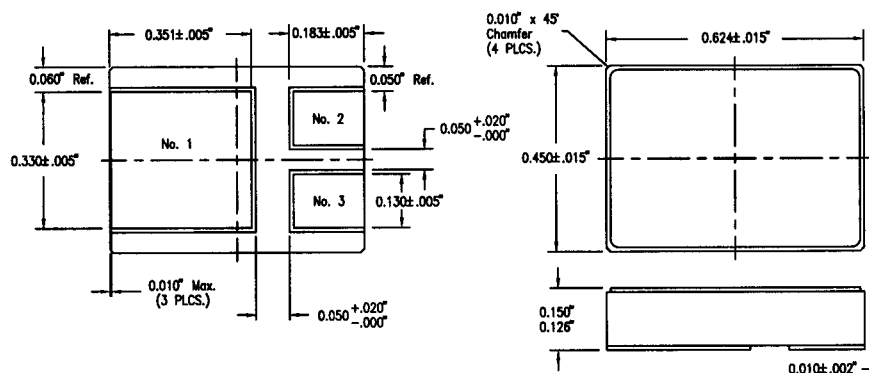
8 AMP
800 VOLTS
1.2 Ω
N-CHANNEL
POWER MOSFET

MILPACK**MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	800	Volts
Gate to Source Voltage	V _{GS}	±30	Volts
Continuous Drain Current @TC=25°C @TC=100°C	I _D	8 ---	Amps
Operating and Storage Temperature	Top & Tstg	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	1.25	°C/W
Total Device Dissipation @ TC=25°C Total Device Dissipation @ TC=55°C	P _D	100 76	Watts
Single Pulse Avalanche Energy	E _{AS}	---	mJ
Repetitive Avalanche Energy	E _{AR}	---	mJ

PACKAGE OUTLINE: MILPACK

PIN OUT:
PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00299 A**MED**

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ELECTRICAL CHARACTERISTICS @ T_J=25°C (Unless Otherwise Specified)

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (V _{GS} =0 V, I _D =250μA)		BV _{DSS}	800	---	---	V
Temperature Coefficient of Breakdown Voltage		$\frac{\Delta BV_{DSS}}{\Delta T_J}$	---	---	---	V/°C
Drain to Source on State Resistance (V _{GS} =10 V)	I _D =4 A I _D =--- A	R _{DS(on)}		0.85 ---	1.2 ---	Ω
Gate Threshold Voltage (V _{DS} =V _{GS} , I _D =250μA)		V _{GS(th)}	2	3.5	4	V
Forward Transconductance (V _{DS} =V _{GS} , I _{DS} =---A)		g _{fs}	---	---	---	S(Ω)
Zero Gate Voltage Drain Current (V _{DS} =80% rated voltage, V _{GS} =0 V) (V _{DS} =80% rated V _{DS} , V _{GS} =0 V, T _A =125°C)		I _{DSS}	---	---	0.25 1	mA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated V _{GS}	I _{GSS}	---	---	100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	V _{GS} =10 Volts 50% rated V _{DS} Rated I _D	Q _g Q _{gs} Q _{gd}	---	76 6 45	105 11 49	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	V _{DD} =50% rated V _{DS} rated I _D R _G =6.2Ω	t _{d(on)} t _r t _{d(off)} t _f	---	22 30 55 20	30 45 81 39	nsec
Diode Forward Voltage (I _S =rated I _D , V _{GS} =0 V, T _J =25°C)		V _{SD}	---	0.85	1.3	V
Diode Reverse Recovery Time Reverse Recovery Charge	T _J =25°C I _F =rated I _D di/dt=100 A/μsec	t _{rr} Q _{RR}	240 1.7	360 3.4	960 7	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{GS} =0 Volts V _{DS} =25 Volts f= 1 MHz	C _{iss} C _{oss} C _{rss}	---	1600 260 90	1800 330 127	pF